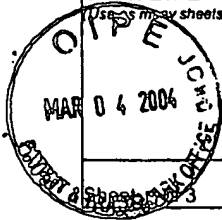


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Complete if Known	
Application Number	10/042,924
Filing Date	January 9, 2002
First Named Inventor	Forbes, Leonard
Group Art Unit	2813
Examiner Name	Vesperman, William
Attorney Docket No: 303.684US2	

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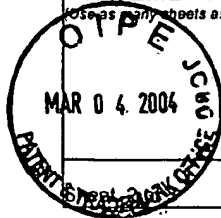
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Application Number	10/042,924
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First Named Inventor	Forbes, Leonard
Group Art Unit	2813
Examiner Name	Vesperman, William

Attorney Docket No: 303.684US2

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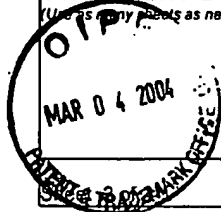
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Application Number	10/042,924
Filing Date	January 9, 2002
First Named Inventor	Forbes, Leonard
Group Art Unit	2813
Examiner Name	Vesperman, William

Attorney Docket No: 303.684US2

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

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*William Vesperman*

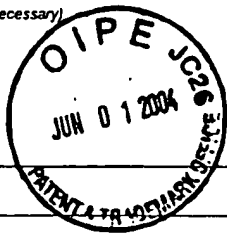
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Application Number	10/042924
Filing Date	January 9, 2002
First Named Inventor	Forbes, Leonard
Group Art Unit	2813
Examiner Name	Vesperman, William

Attorney Docket No: 303.684US2

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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WV	US-6,730,960	05/04/2004	Forbes, L.	257	321	08/30/2001

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